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NDD03N40Z, NDT03N40Z

N-Channel Power MOSFET 400 V, 3.4 Ω

Features

- 100% Avalanche Tested
- Extremely High dv/dt Capability
- Gate Charge Minimized
- Very Low Intrinsic Capacitance
- Improved Diode Reverse Recovery Characteristics
- Zener-protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	NDD	NDT	Unit
Drain-to-Source Voltage	V_{DS}	400		V
Gate-to-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current Steady State, $T_C = 25^\circ\text{C}$ (Note 1)	I_D	2.1	0.5	A
Continuous Drain Current Steady State, $T_C = 100^\circ\text{C}$ (Note 1)	I_D	1.3	0.3	A
Power Dissipation Steady State, $T_C = 25^\circ\text{C}$	P_D	37	2.0	W
Pulsed Drain Current	I_{DM}	8.0	7.2	A
Continuous Source Current (Body Diode)	I_S	2.1	0.5	A
Single Pulse Drain-to-Source Avalanche Energy ($I_D = 1\text{ A}$)	EAS	42		mJ
Peak Diode Recovery (Note 2)	dV/dt	12		V/ns
Maximum Temperature for Soldering Leads	T_L	260		$^\circ\text{C}$
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to $+150$		$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Limited by maximum junction temperature
2. $I_S \leq 2.4\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) NDD03N40Z	$R_{\theta JC}$	3.4	$^\circ\text{C}/\text{W}$
Junction-to-Ambient Steady State	$R_{\theta JA}$		$^\circ\text{C}/\text{W}$
NDD03N40Z (Note 4)		42	
NDD03N40Z-1 (Note 3)		96	
NDT03N40Z (Note 4)		62	
NDT03N40Z (Note 5)		149	

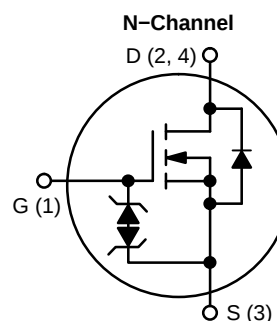
3. Insertion mounted
4. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127" sq. [2 oz] including traces)
5. Surface-mounted on FR4 board using minimum recommended pad size (Cu area = 0.026" sq. [2 oz]).



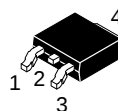
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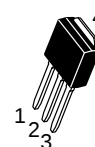
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$
400 V	3.4 Ω @ 10 V



SOT-223
CASE 318E
STYLE 3



DPAK
CASE 369C
STYLE 2



IPAK
CASE 369D
STYLE 2

MARKING & ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

NDD03N40Z, NDT03N40Z

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	400			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	Reference to 25°C, I _D = 1 mA		450		mV/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V	T _J = 25°C		1	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V			±10	μA

ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 50 μA	3.0	3.9	4.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	Reference to 25°C, I _D = 50 μA		9.8		mV/°C
Static Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.6 A		3.0	3.4	Ω
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 0.6 A		1.2		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 7)	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		140		pF
Output Capacitance (Note 7)	C _{oss}			17		
Reverse Transfer Capacitance (Note 7)	C _{rss}			3.0		
Effective output capacitance, energy related (Note 9)	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 to 320 V		10		
Effective output capacitance, time related (Note 10)	C _{o(tr)}	I _D = constant, V _{GS} = 0 V, V _{DS} = 0 to 320 V		20		
Total Gate Charge (Note 7)	Q _g	V _{DS} = 200 V, I _D = 2.4 A, V _{GS} = 10 V		6.6		nC
Gate-to-Source Charge (Note 7)	Q _{gs}			1.7		
Gate-to-Drain ("Miller") Charge (Note 7)	Q _{gd}			3.5		
Plateau Voltage	V _{GP}			6.9		V
Gate Resistance	R _g			9.0		Ω

RESISTIVE SWITCHING CHARACTERISTICS (Note 8)

Turn-on Delay Time	t _{d(on)}	V _{DD} = 200 V, I _D = 2.4 A, V _{GS} = 10 V, R _G = 0 Ω		10		ns
Rise Time	t _r			7.0		
Turn-off Delay Time	t _{d(off)}			13		
Fall Time	t _f			5.0		

SOURCE-DRAIN DIODE CHARACTERISTICS

Diode Forward Voltage	V _{SD}	I _S = 0.5 A, V _{GS} = 0 V	T _J = 25°C		0.8	1.5	V
			T _J = 100°C		0.7		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V, I _S = 2.4 A, d _i /d _t = 100 A/μs			152		ns
Charge Time	t _a				62		
Discharge Time	t _b				90		
Reverse Recovery Charge	Q _{rr}				452		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

7. Guaranteed by design.

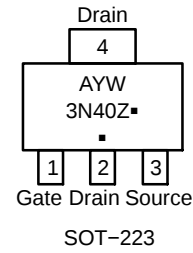
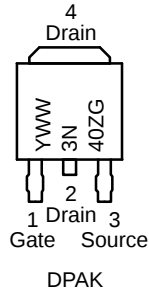
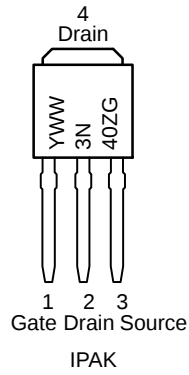
8. Switching characteristics are independent of operating junction temperatures.

9. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

10. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

NDD03N40Z, NDT03N40Z

MARKING DIAGRAMS



A = Assembly Location
Y = Year
W, WW = Work Week
3N40Z = Specific Device Code
G or ■ = Pb-Free Package
(*Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NDD03N40Z-1G	IPAK (Pb-Free, Halogen Free)	75 Units / Rail
NDD03N40ZT4G	DPAK (Pb-Free, Halogen Free)	2500 / Tape & Reel
NDT03N40ZT1G	SOT-223 (Pb-Free, Halogen Free)	1000 / Tape & Reel
NDT03N40ZT3G	SOT-223 (Pb-Free, Halogen Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

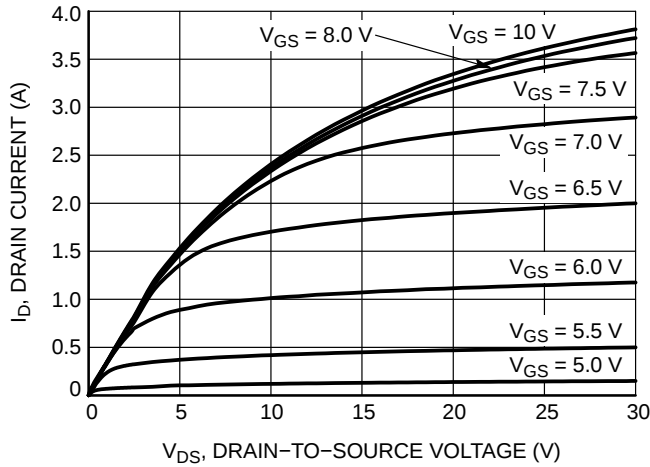


Figure 1. On-Region Characteristics

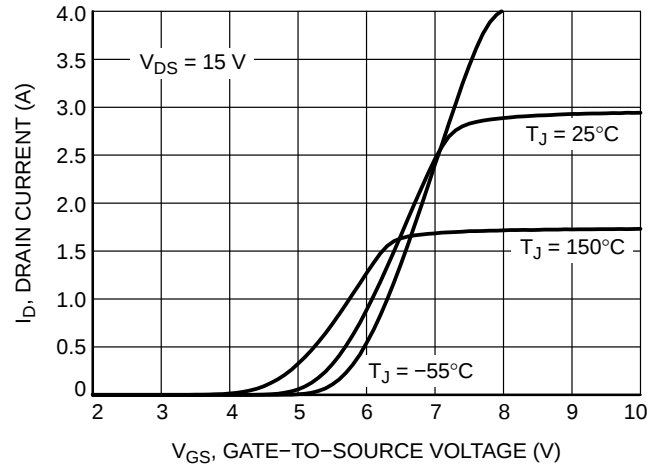


Figure 2. Transfer Characteristics

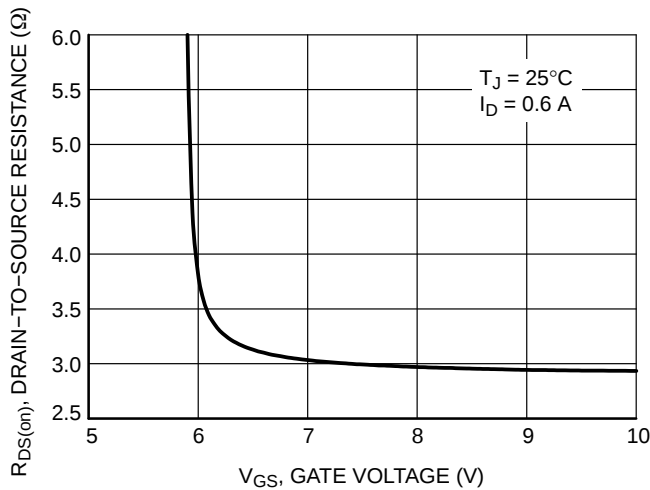


Figure 3. On-Resistance vs. Gate-to-Source Voltage

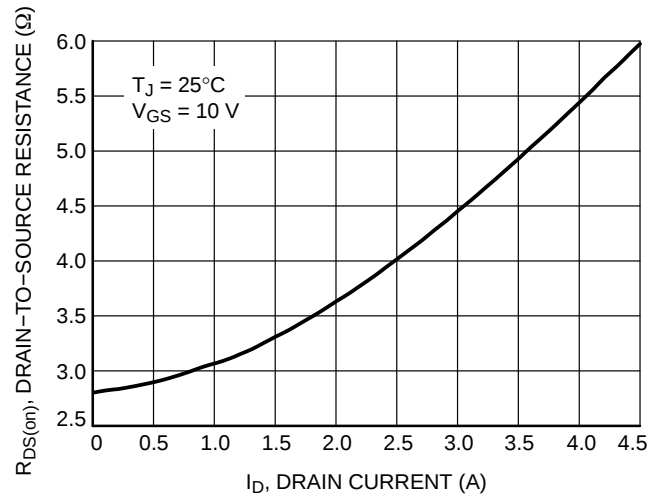


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

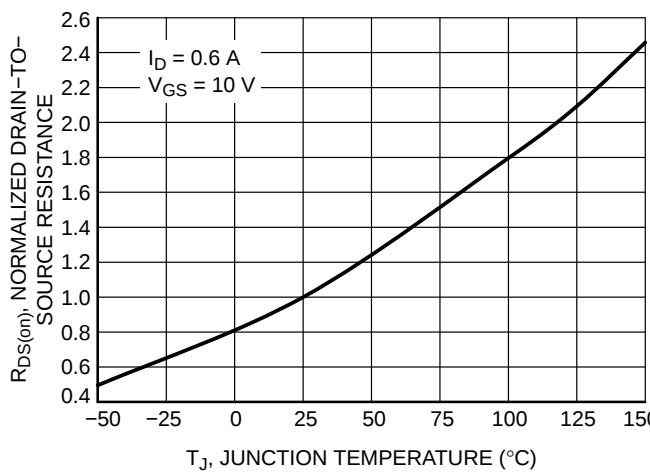


Figure 5. On-Resistance Variation with Temperature

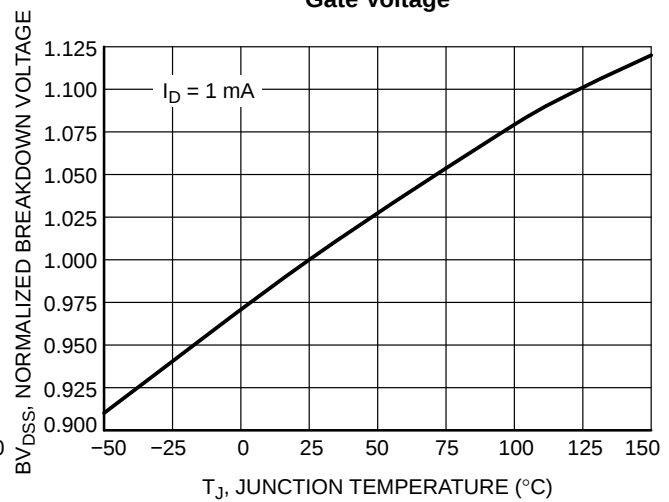


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

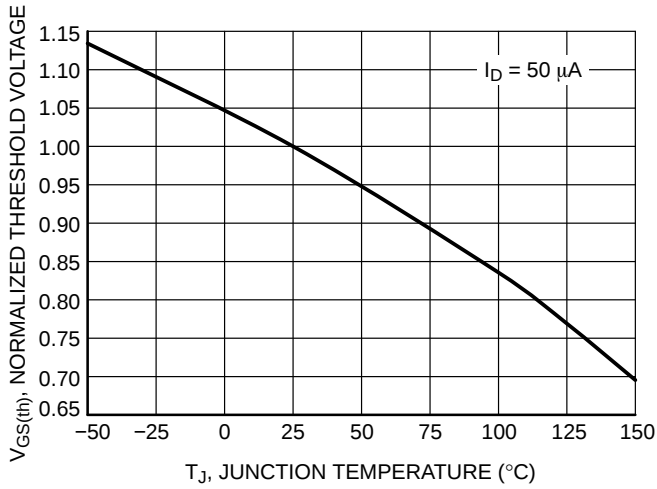


Figure 7. Threshold Voltage Variation with Temperature

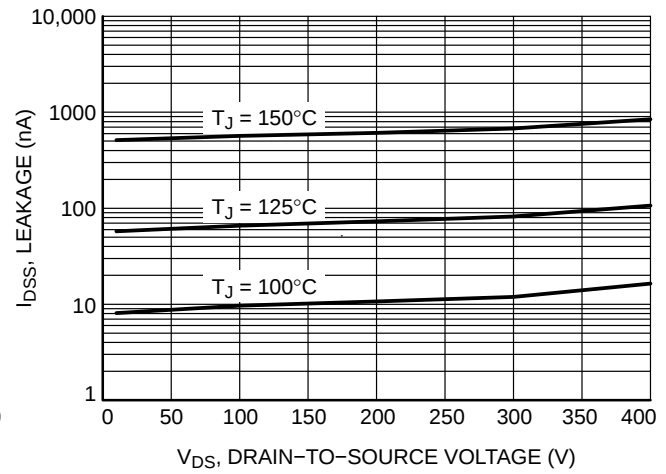


Figure 8. Drain-to-Source Leakage Current vs. Voltage

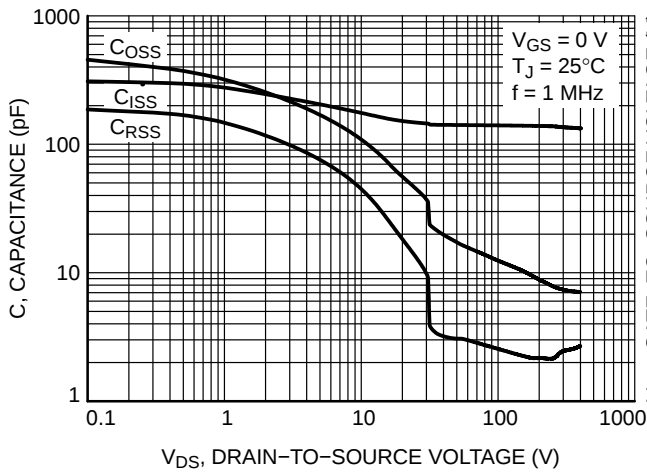


Figure 9. Capacitance Variation

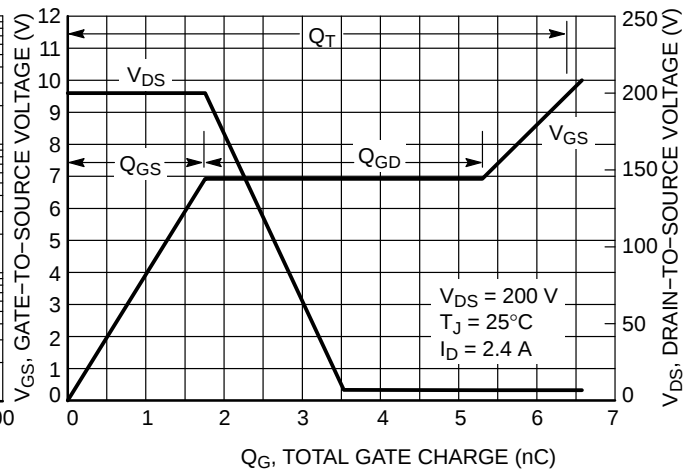


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

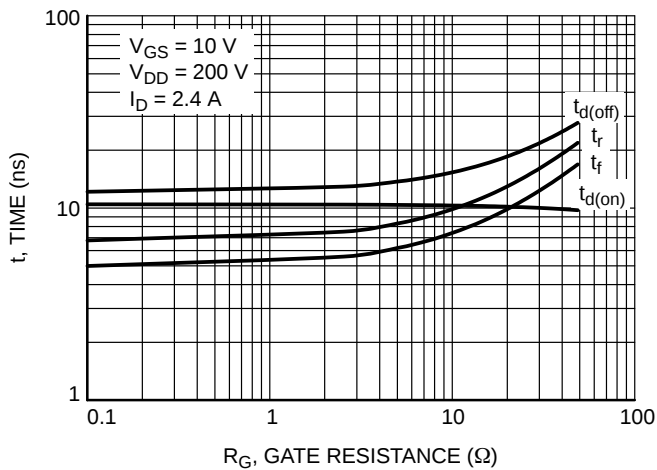


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

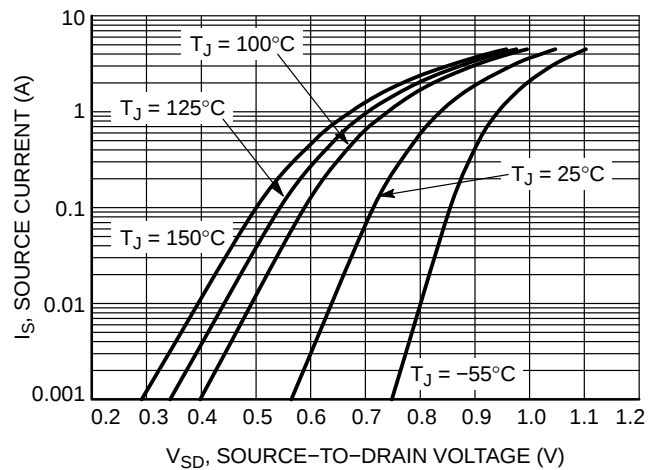


Figure 12. Diode Forward Voltage vs. Current

NDD03N40Z, NDT03N40Z

TYPICAL CHARACTERISTICS

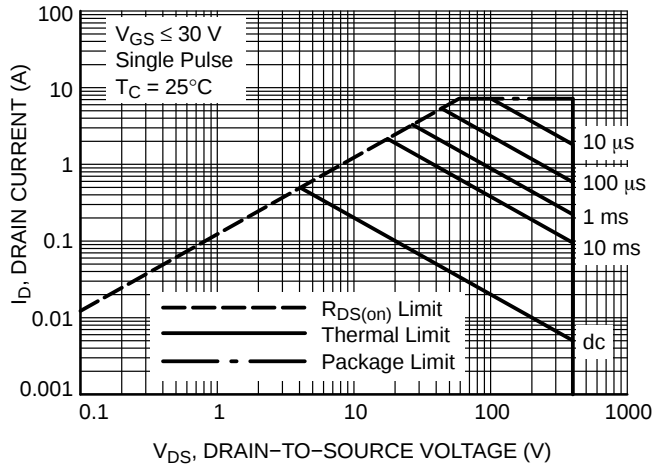


Figure 13. Maximum Rated Forward Biased Safe Operating Area for NDT03N40Z

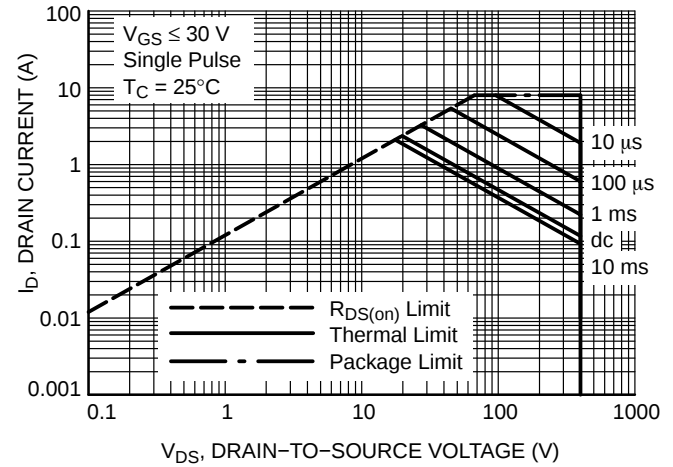


Figure 14. Maximum Rated Forward Biased Safe Operating Area for NDD03N40Z

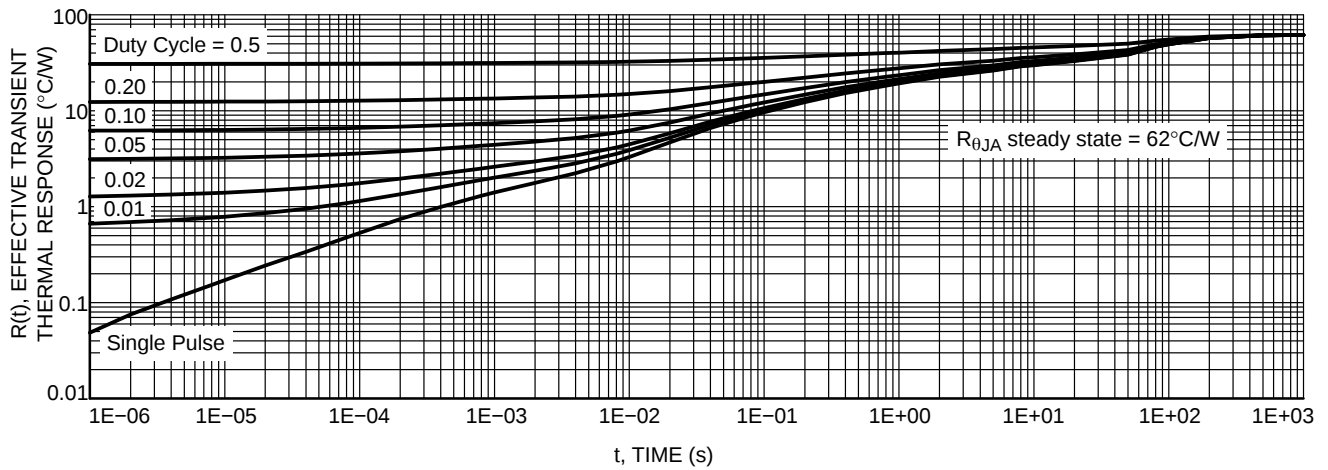


Figure 15. Thermal Impedance (Junction-to-Ambient) for NDT03N40Z

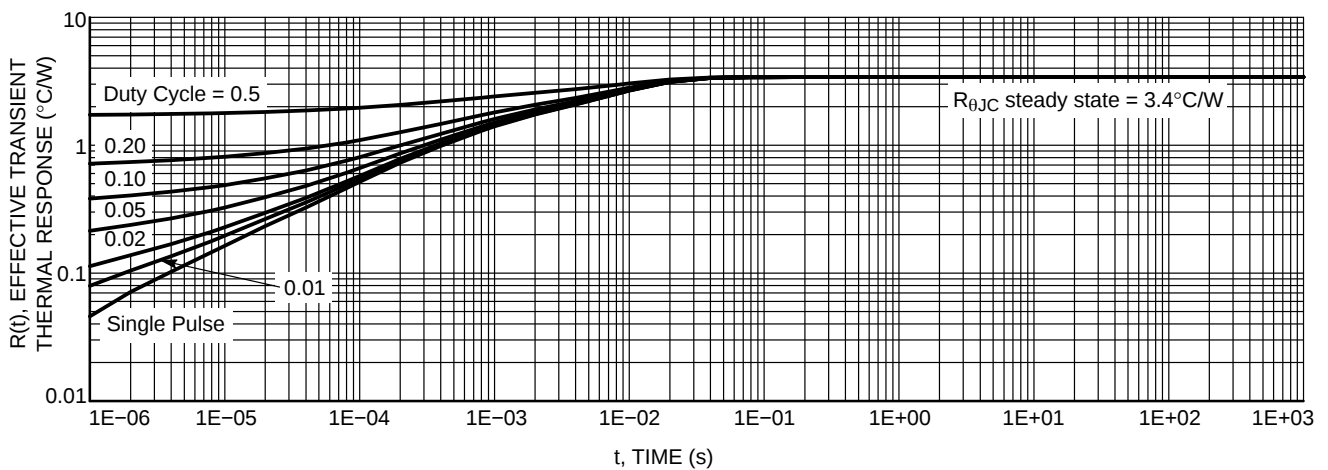
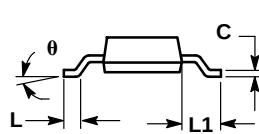
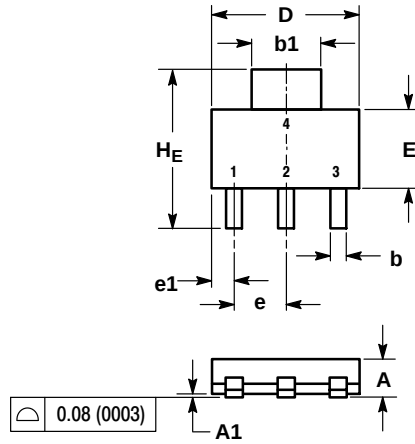


Figure 16. Thermal Impedance (Junction-to-Case) for NDD03N40Z

NDD03N40Z, NDT03N40Z

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N



NOTES:

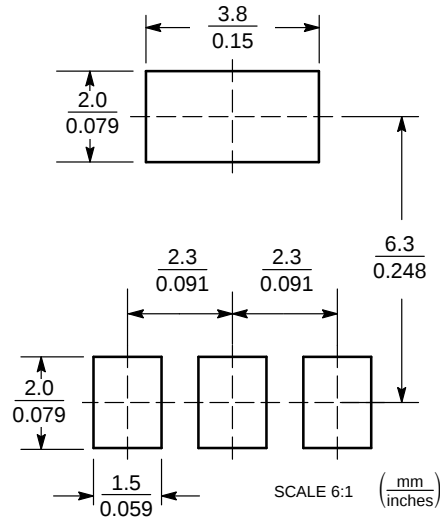
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	—	10°	0°	—	10°

STYLE 3:

- PIN 1: GATE
2: DRAIN
3: SOURCE
4: DRAIN

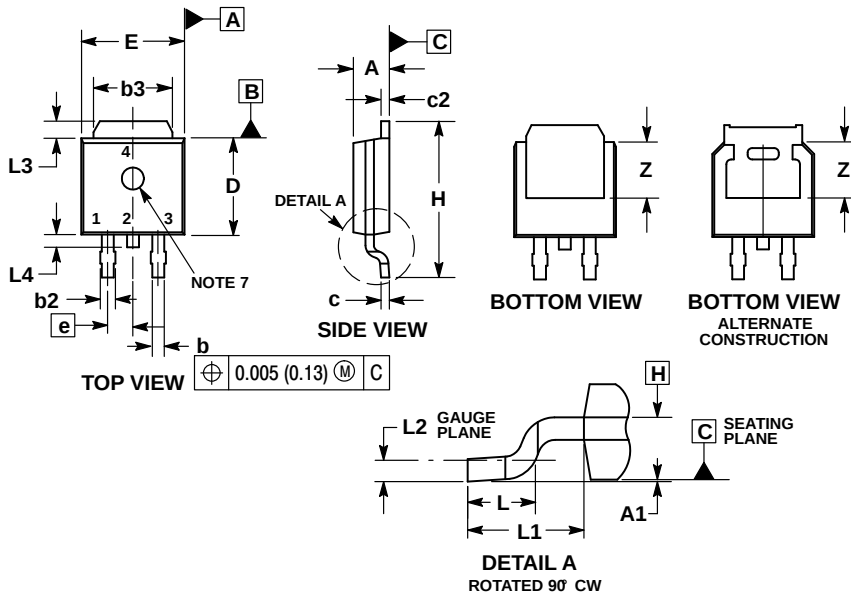
SOLDERING FOOTPRINT



NDD03N40Z, NDT03N40Z

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE E



NOTES:

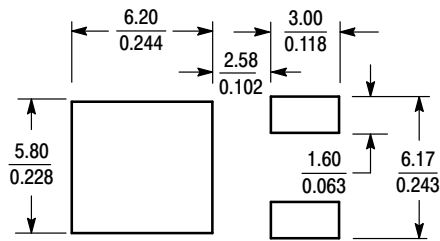
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

SOLDERING FOOTPRINT*



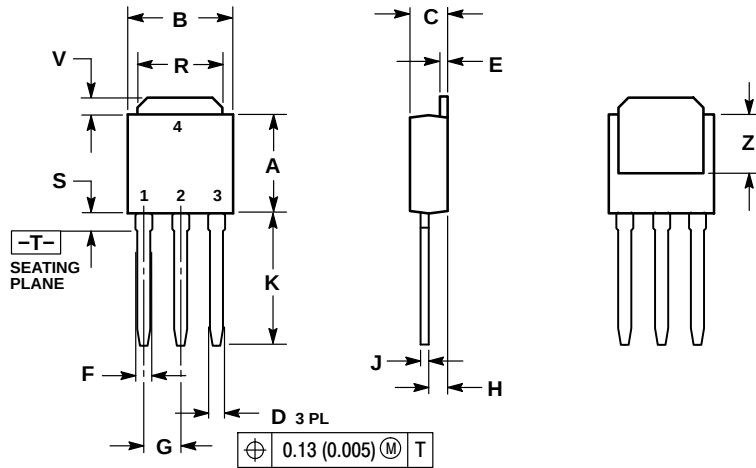
SCALE 3:1 (mm / inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NDD03N40Z, NDT03N40Z

PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1: GATE
2: DRAIN
3: SOURCE
4: DRAIN

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NDD03N40Z/D